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Bib Data Sheet

SERIAL NUMBER 10/717,149	FILING DATE 11/18/2003 RULE	CLASS 438	GROUP ART UNIT 2818	ATTORNEY DOCKET NO. ATM-262	
APPLICANTS Alan L. Renninger, Cupertino, CA; James J. Shen, Colorado Springs, CO; ** CONTINUING DATA ***** N/A ** FOREIGN APPLICATIONS ***** N/A IF REQUIRED, FOREIGN FILING LICENSE GRANTED ** 02/17/2004					
Foreign Priority claimed <input type="checkbox"/> yes <input checked="" type="checkbox"/> no 35 USC 119 (a-d) conditions met <input checked="" type="checkbox"/> yes <input type="checkbox"/> no <input type="checkbox"/> Met after Allowance Verified and Acknowledged <u> </u> Examiner's Signature Initials		STATE OR COUNTRY CA	SHEETS DRAWING 3	TOTAL CLAIMS 24	INDEPENDENT CLAIMS 4
ADDRESS 003897 SCHNECK & SCHNECK P.O. BOX 2-E SAN JOSE, CA 95109-0005					
TITLE <i>Method of Forming a low voltage gate oxide layer and Embedded EEPROM cell and method of forming the same tunnel oxide layer in an EEPROM cell.</i>					
FILING FEE RECEIVED 1054	FEES: Authority has been given in Paper No. _____ to charge/credit DEPOSIT ACCOUNT No. _____ for following:		<input type="checkbox"/> All Fees <input type="checkbox"/> 1.16 Fees (Filing) <input type="checkbox"/> 1.17 Fees (Processing Ext. of time) <input type="checkbox"/> 1.18 Fees (Issue)		

In the Title:

Please replace the title with:

METHOD OF FORMING A LOW VOLTAGE GATE OXIDE LAYER AND TUNNEL
OXIDE LAYER IN AN EEPROM CELL